

2N2221
2N2222

**SILICON
NPN TRANSISTORS**



TO-18 CASE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2221 and 2N2222 are silicon NPN epitaxial planar transistors designed for small signal, general purpose switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Power Dissipation ($T_C=25^\circ\text{C}$)
Operating and Storage Junction Temperature
Thermal Resistance
Thermal Resistance

SYMBOL

V_{CBO}	60
V_{CEO}	30
V_{EBO}	5.0
I_C	800
P_D	500
P_D	1.2
T_J, T_{stg}	-65 to +200
θ_{JA}	350
θ_{JC}	146

UNITS

V
V
V
mA
mW
W
$^\circ\text{C}$
$^\circ\text{C/W}$
$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=50\text{V}$	-	10	nA
I_{CBO}	$V_{CB}=50\text{V}, T_A=150^\circ\text{C}$	-	10	μA
I_{EBO}	$V_{EB}=3.0\text{V}$	-	10	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60	-	V
BV_{CEO}	$I_C=10\text{mA}$	30	-	V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0	-	V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.4	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	1.6	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	1.3	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	2.6	V
f_T	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	250	-	MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$	-	8.0	pF
C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=100\text{kHz}$	-	30	pF

2N2221
2N2222

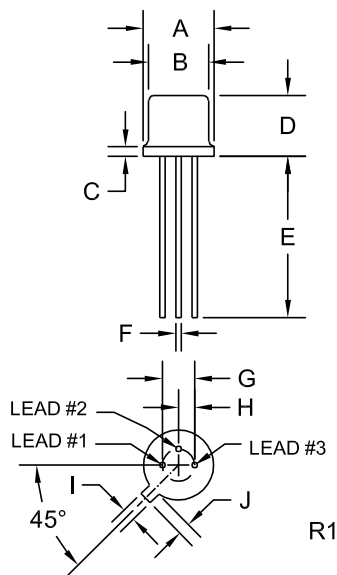
SILICON
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N2221		2N2222	
		MIN	MAX	MIN	MAX
h_{FE}	$V_{CE}=10\text{V}$, $I_C=0.1\text{mA}$	20	-	35	-
h_{FE}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$	25	-	50	-
h_{FE}	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$	35	-	75	-
h_{FE}	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $T_A=-55^{\circ}\text{C}$	15	-	35	-
h_{FE}	$V_{CE}=10\text{V}$, $I_C=150\text{mA}$	40	120	100	300
h_{FE}	$V_{CE}=1.0\text{V}$, $I_C=150\text{mA}$	20	-	50	-
h_{FE}	$V_{CE}=10\text{V}$, $I_C=500\text{mA}$	25	-	40	-

TO-18 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R2 (24-July 2013)

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

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- Application notes
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CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
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